



# LESD8D5.0CN3T5G ESD PROTECTION DIODE

## Discription

The LESD8D5.0CN3T5G is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time ,make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

### **Applications**

- I Cellular phones audio
- I MP3 players
- I Digital cameras
- I Portable applicationss
- I mobile telephone

### Features

- Small Body Outline Dimensions:
  0.039" X 0.024"(1.0mmX0.6mm)
- Low Body Height: 0.020"(0.50mm)
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- These are Pb-Free Devices
- We declare that the material of product compliance with RoHS requirements.

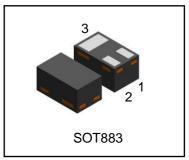
### MAXIMUM RATINGS

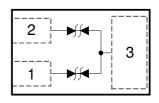
Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Air discharge Contact discharge		±25 ±20	kV kV
ESD Voltage Per Human Body Model		16	kV
Total Power Dissipation on FR-5 Board (Note 1)	PD	200	mW
@ T <sub>A</sub> =25℃			
Junction and Storage Temperature Range	TJ,TSTG	-55 to 150	°C
Lead Solder Temperature – Maximum (10	TL	260	°C
Second Duration)			

Stresses exceeding Maximum Ratings may damage the device. Maximum Rating are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = 1.0\*0.75\*0.62 in.







### Ordering information

Device	Marking	Shipping	
LESD8D5.0CN3T5G	P2	10000/Tape&Reel	

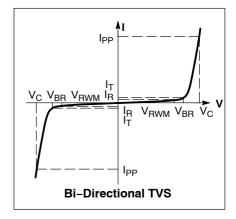


## LESD8D5.0CN3T5G

#### ELECTRICAL CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter		
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current		
V <sub>C</sub>	Clamping Voltage @ IPP		
V <sub>RWM</sub>	Working Peak Reverse Voltage		
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>		
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>		
Ι <sub>Τ</sub>	Test Current		
P <sub>pk</sub>	Peak Power Dissipation		
С	Capacitance @ $V_R = 0$ and f = 1.0 MHz		



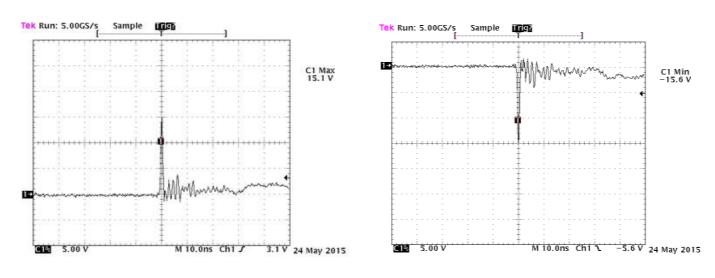
#### ELECTRICAL CHARACTERISTICS

	V <sub>RWM</sub> (V)	I <sub>R1</sub> (μΑ) @ V <sub>RWM</sub>	I <sub>R2</sub> (μΑ) @ V <sub>R</sub> =3.5∨	V <sub>BR</sub> (V) @ 叶 (Note 2)	ΙŢ	V <sub>C</sub> (V) @ I <sub>PP</sub> = 1 A (Note 3)	V <sub>C</sub> (V) @MAX I <sub>PP</sub> (Note 3)	I <sub>PP</sub> (A) (Note 3)	<b>Р<sub>РК</sub>(W)</b> (Note 3)	С (рF)
Device	Max	Max	Max	Min	mA	Max	Max	Max	Мах	Max
LESD8D5.0CN3T5G	5.0	0.5	0.3	5.6	1.0	9.8	12.5	5.5	69	15

Other voltage available upon request.

2.  $V_{BR}$  is measured with a pulse test current IT at an ambient temperature of  $25\,^\circ\!\!\mathbb{C}$ 

3. Surge current waveform per Figure 3.



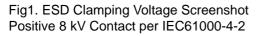


Fig2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2



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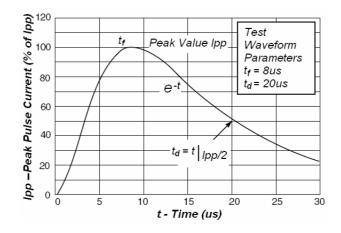


Fig3. Pulse Waveform

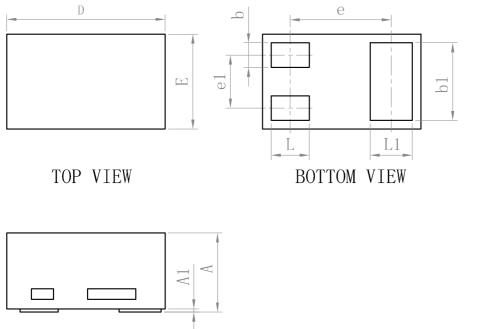




# LESD8D5.0CN3T5G

**SOT883** 

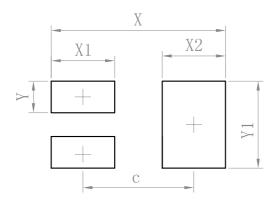
## Package Outline Dimension



SOT883					
Dim	Min	Тур	Max		
D	0.95	1.00	1.05		
Е	0.55	0.60	0.65		
е	I	0.64	-		
e1	I	0.34	-		
L	0.19	0.24	0.29		
L1	0.22	0.27	0.32		
b	0.10	0.15	0.20		
b1	0.44	0.49	0.54		
А	0.43	0.48	0.53		
A1	0	-	0.05		
All Dimensions in mm					

SIDE VIEW

## Suggested Pad layout



Dimensions	(mm)
с	0.70
Х	1.10
X1	0.40
X2	0.40
Y	0.20
¥1	0.55